Microprobe-enabled Terahertz sensing applications

World of Photonics, Laser 2015, Munich

Protemics GmbH Aachen, Germany



Terahertz microprobing technology:

Taking advantage of Terahertz range benefits without being compromised by wavelength-based resolution limitations.

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Terahertz Research	Thin-film Analysis	Chip-Testing	Volume Screening
Application areas:	Application areas:	Application areas:	Application areas:
 Metamaterials Plasmonics Devices Waveguides Sensor surfaces Graphene 	 Solar cells Displays Flexible electronics Doping layers Graphene Transparent conductors 	 Time-domain reflectometry Fault isolation Packaging level inspection 3D integration Through silicon via (TSV) 	 Plastic weld inspection Fiber inforced polymers Chip underfill inspection Organic layer screening
Benefits: • Near-field access • High-sensitivity • Low-invasiveness • Polarisation sensitive • Broadband	Benefits: • Sheet resistance imaging • Contactless • Micron-scale resolution • Large-area scanning • High-speed scanning	Benefits: • Market leading TDR resolution • Contactless • Non-destructive • Cost advantage	 Benefits: Non-destructive Fast inspection Screening of opaque plastics Detection of microdefects

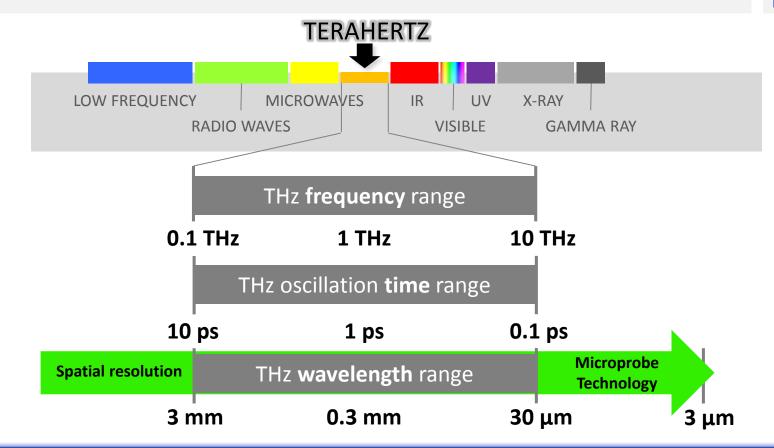


Outline

- Introduction
 - Mismatch between THz radiation wavelengths and micro/nanostructure size
- <u>THz microprobes</u>
 - Working principle
- Thin-film analysis with sub-wavelength resolution on large areas
 - Thin-film conductors (Metals, Graphene, Semiconductors, ITO and ITO-replacement materials)
- THz Metamaterials
 - THz-Metamaterials, Metamaterial-based sensing
- Plastic laser weld inspection
 - Near-field detection of micro-defects
- <u>THz device analysis</u>
 - THz on-chip device characterization
 - Failure localization in chip packages



Introduction





Introduction

Large THz wavelengths are problematic:

- When structures under test are too small (similar to λ or even smaller)
 - Lateral Micro/Nanostructures (Solar cells, electronic structures, micro defects, ...)
 - Only minute (pl) sample volumes available (-> biosensing)
- On signal transfer to or from THz field confining structures
 - Waveguides
 - Integrated devices

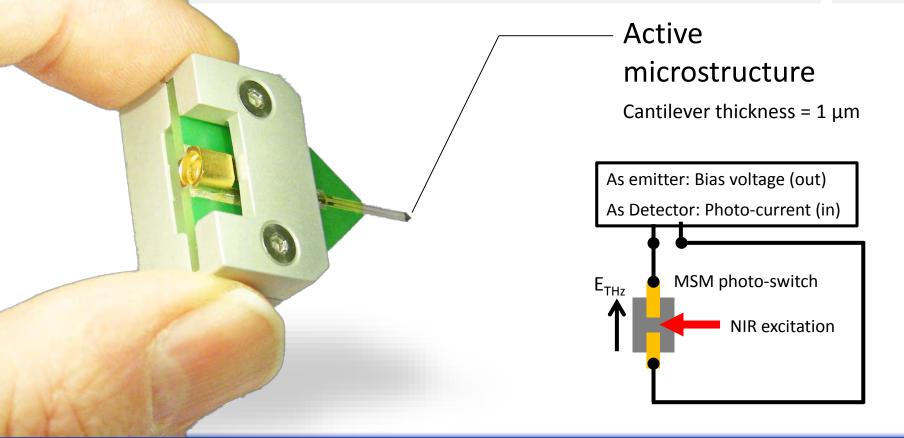
Solution:

- Make THz emitter and/or detector smaller than the wavelength
- Bring the miniaturized emitter/detector in sub-wavelength distance to structure under test



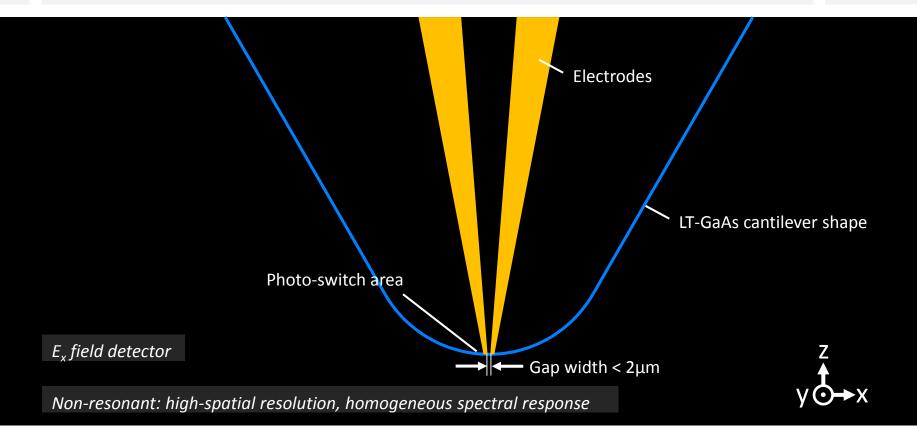
Ultra-fast photoconductive

THz micro-emitters/detectors



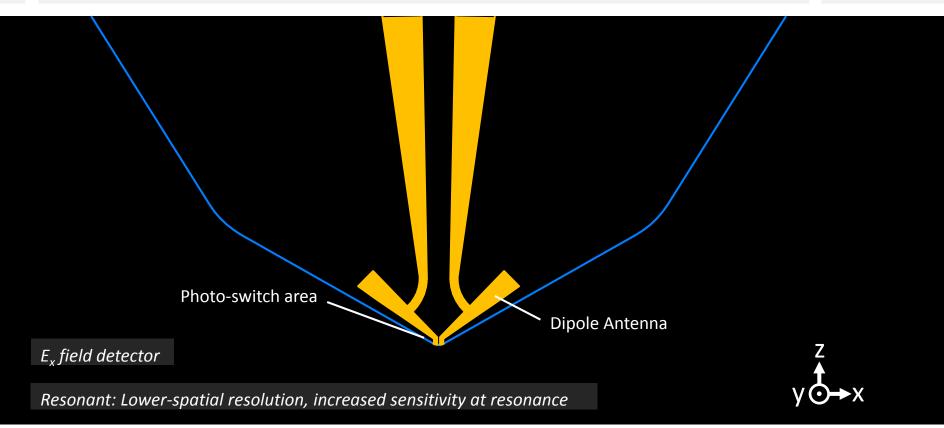


Application specific designs



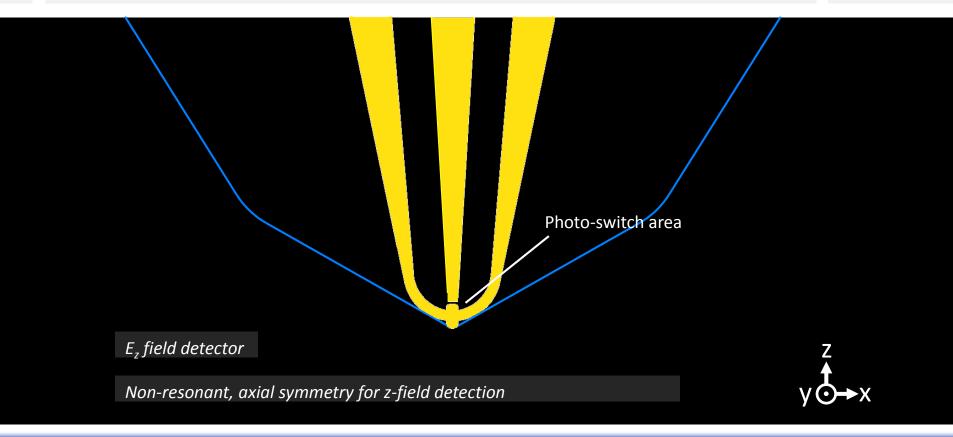


Application specific designs



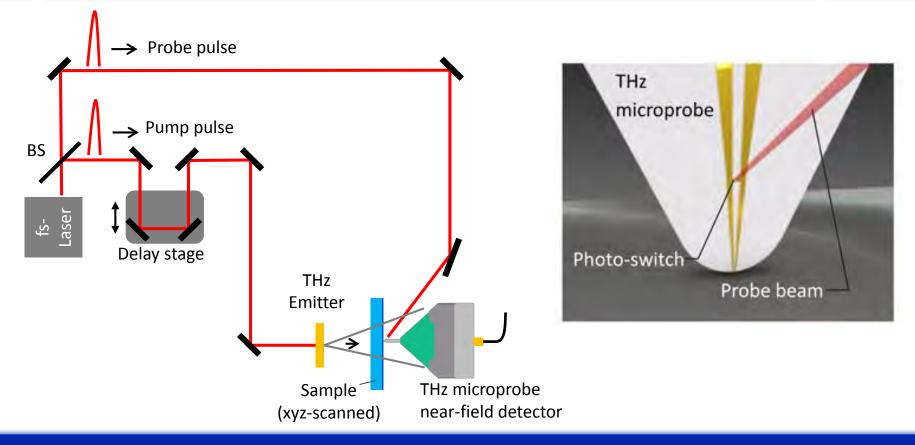


Application specific designs



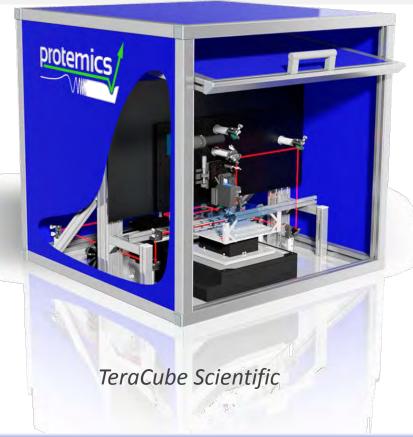


TD near-field sampling





TD near-field system

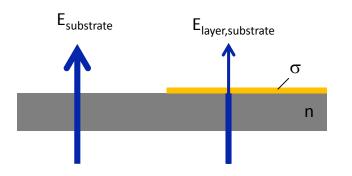


- Automated table-top system
 - 90x90x90 cm box including:
 - Laser
 - Scanning components
 - Opto-mechanics
 - Optics
 - Electronics
 - External components
 - PC
 - Supply unit



Thin-film conductors

- Surface analysis with sub-wavelength resolution on large areas
 - Sheet resistance imaging of thin-film conductors such as
 - <u>Metals</u>
 - <u>Graphene</u>
 - <u>Doped semiconductors</u>
 - Optically transparent conductors: ITO and ITO-replacement materials



Tinkham Formula:				
$E_{layer,substrate}(\omega)$	- 1 + n			
$E_{substrate}(\omega)$	$-\frac{1}{1+n+Z_0\sigma(\omega)d}$			

Accessible sheet resistance range: 0.1 – 10000 Ohm



Thin-film conductors

Short-comings of state-of-the-art sheet-resistance measurement tools

Contact-based four-point probe measurements are problematic:

- On large-bandgap semiconductors (e.g. GaN or SiC)
 -> Imprecise measurements because of nonlinear contacts
- On **passivated** samples (e.g. Solar cells)
 - -> No contact
- On nanostructures (e.g. metal mesh nanostructures)
 -> Requires formation of additional contact pads
- If measurement **time** matters
 - -> Extremely time-consuming (5s/measurement point)
- If non-**destructive**ness matters
 - -> Puncturing from contact needles



Thin-film conductors

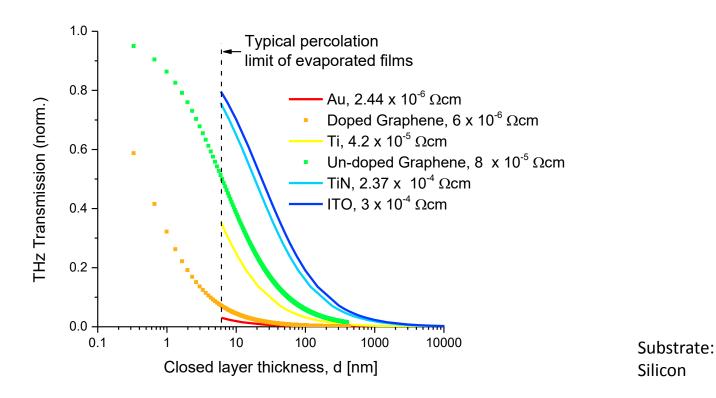
Short-comings of the state-of-the-art sheet-resistance measurement tools

Non-contact Eddy current measurements:

- Spatial resolution is limited to 1 cm for **quantitative** measurements
- Spatial resolution is limited to 2 mm for **qualitative** measurements.



Thin-film conductors





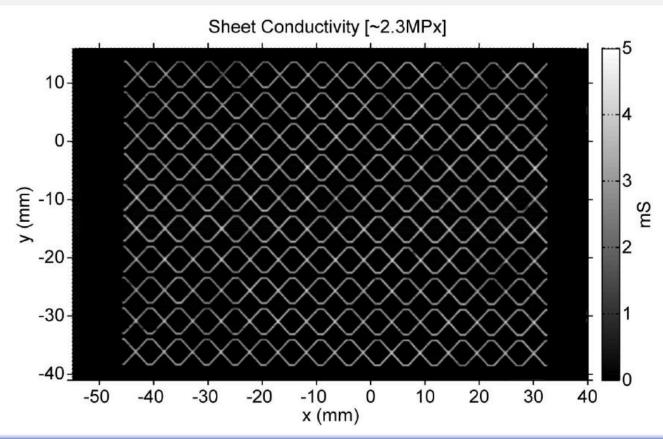
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Thin-film conductors

Measured with THz microprobe Example: Sputtered metal layers with varying thickness on glass -60 Decreasing thickness ,20 (mm) y -40 50 05 05 05 Sheet Resistance [Ω / sq.] 100 Sheet Resistance (mm) k 0 0 10 20 20 40 40 30 -60 -40 -20 -60 20 -40 -20 0 x (mm) x (mm)



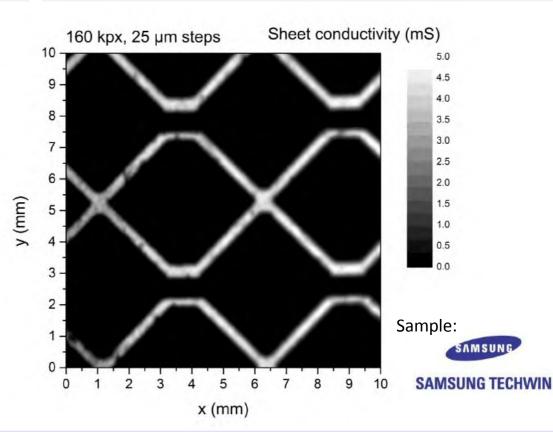
Thin-film conductors: Graphene

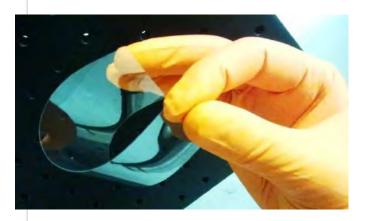




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Thin-film conductors: Graphene



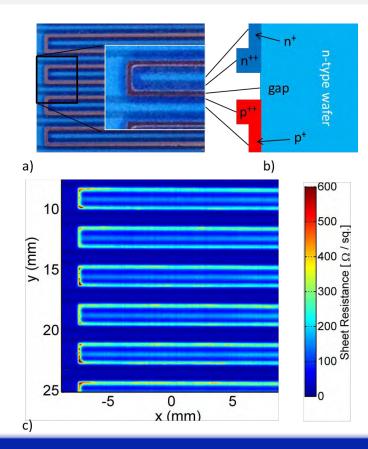


- Graphene pattern on PET foil
- Flexible display application

High-speed contactless raster scanning on **bended** surfaces

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Thin-film conductors: Doped mc-Si

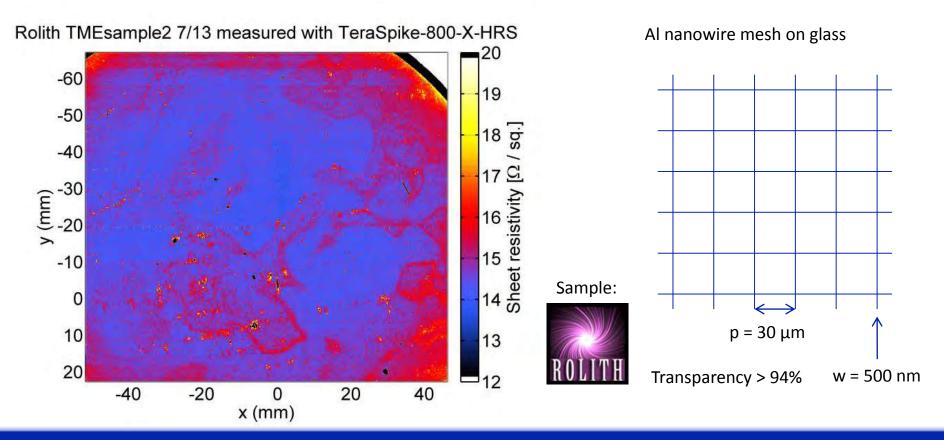


- IBC solar cell structure
- Laser-based material ablation process
- Sheet resistance image reveals areas of process induced inhomogenuity
- Applicable on full cell area and textured surfaces

In collaboration with:

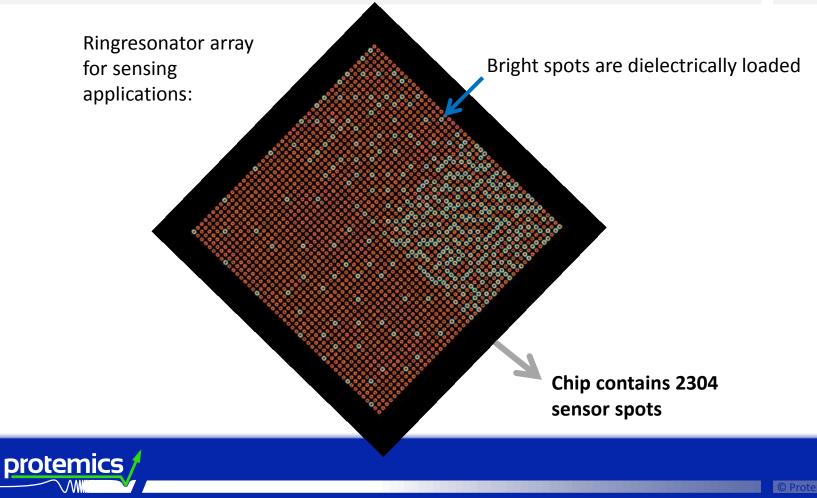


Thin-film conductors: ITO-replacements

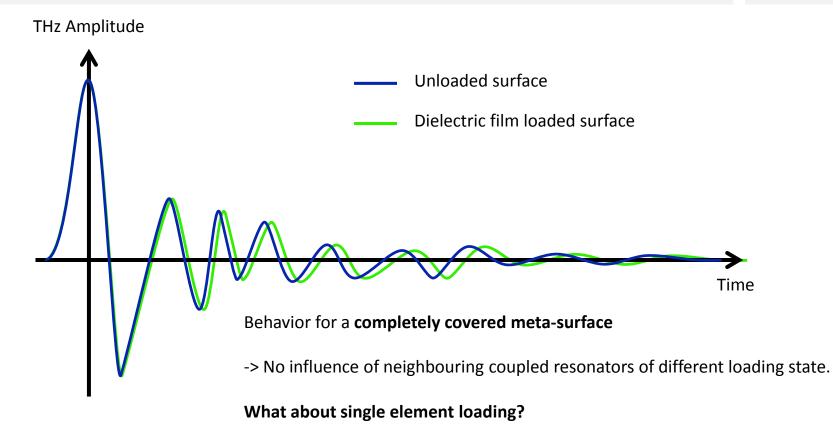




Metamaterials for sensing



Metamaterials for sensing

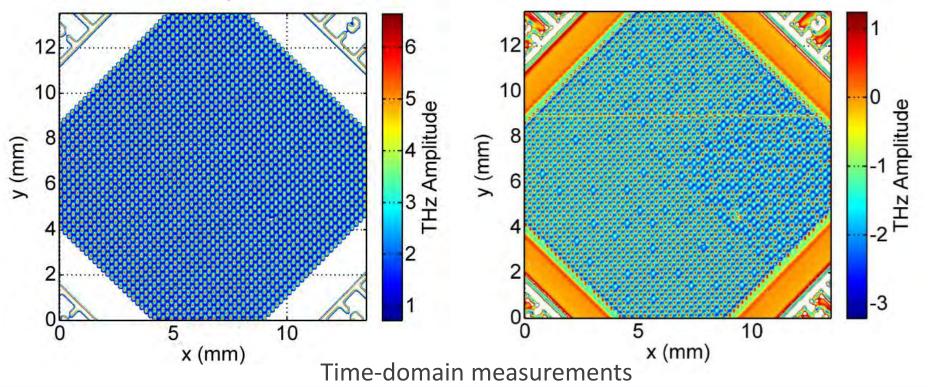




Metamaterials for sensing

t=0.0 ps





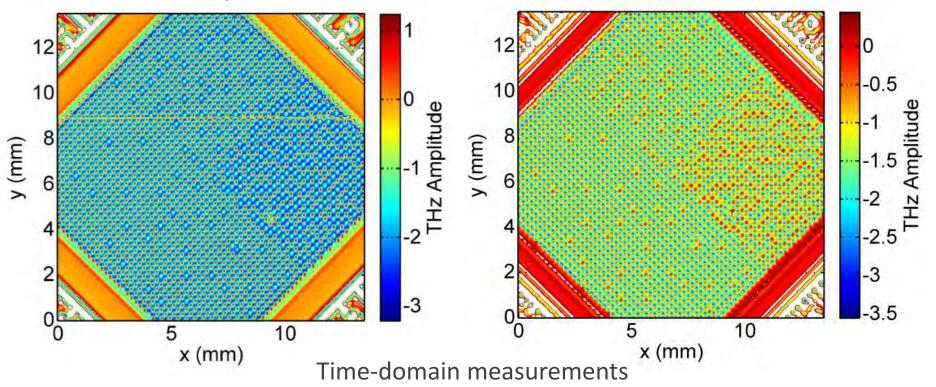


Metamaterials for sensing

t=1.0 ps



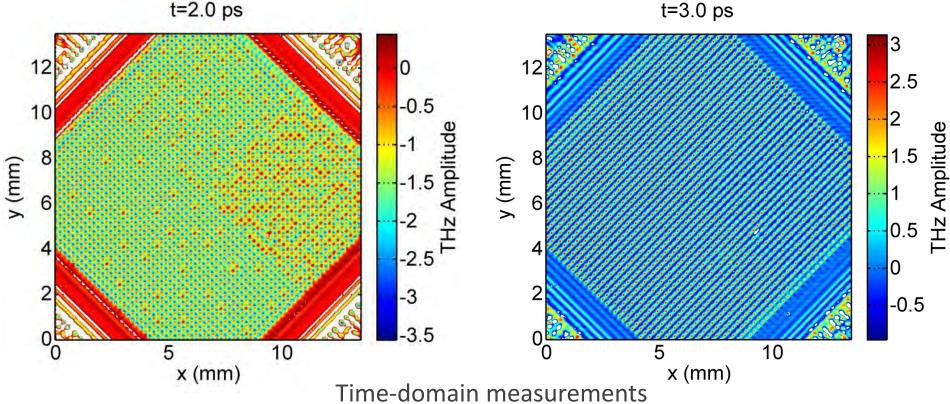
t=2.0 ps





Metamaterials for sensing

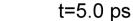
t=2.0 ps

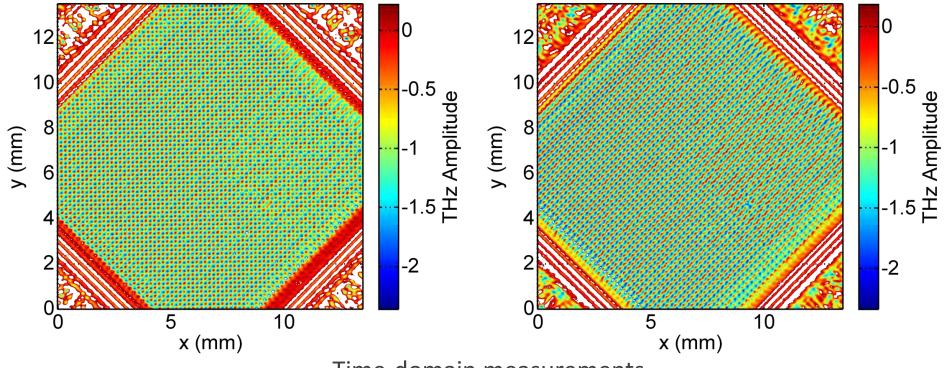




Metamaterials for sensing

t=4.0 ps





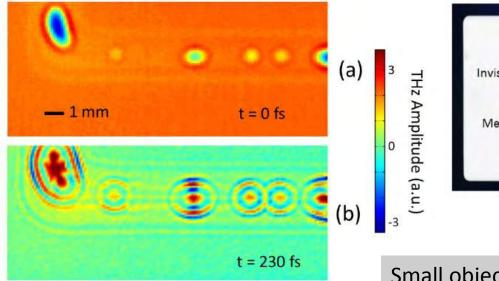
Time-domain measurements

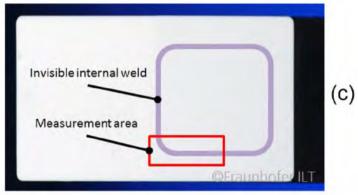


Non-destructive testing

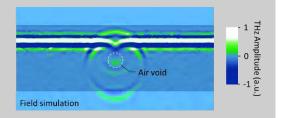
Laser plastic weld inspection

THz microprobe measurement data



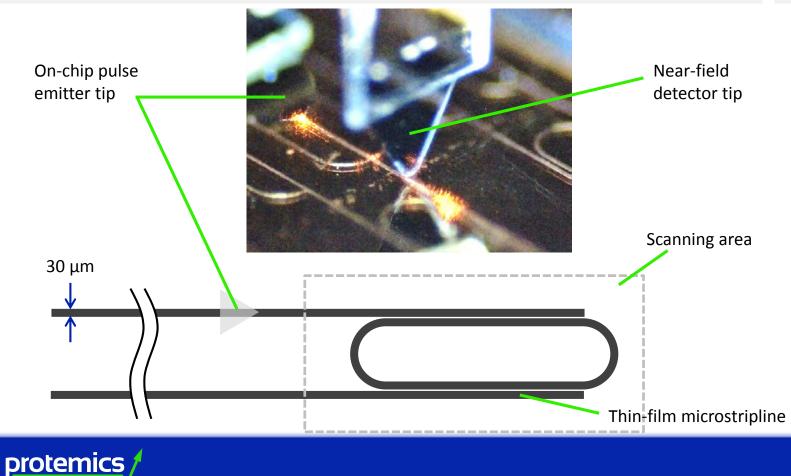


Small objects become visible by scattering light in the near-field:



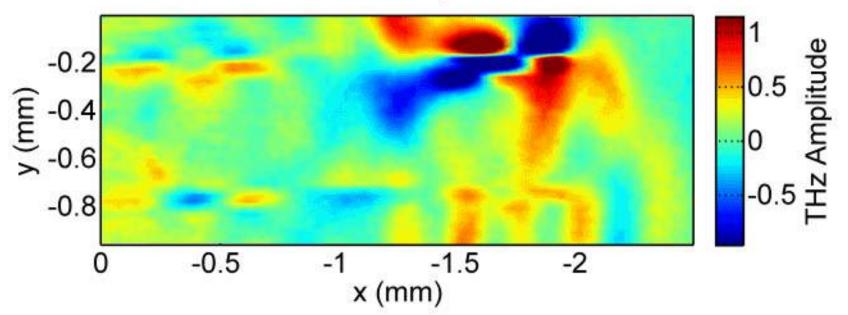


THz on-chip analysis



THz on-chip analysis

t=-0.000 ps

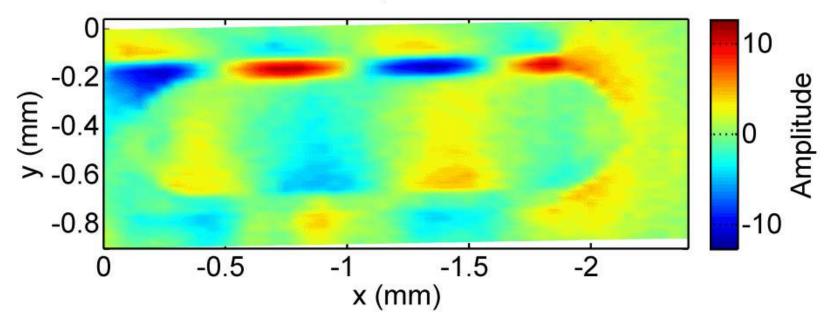


Time-domain measurement



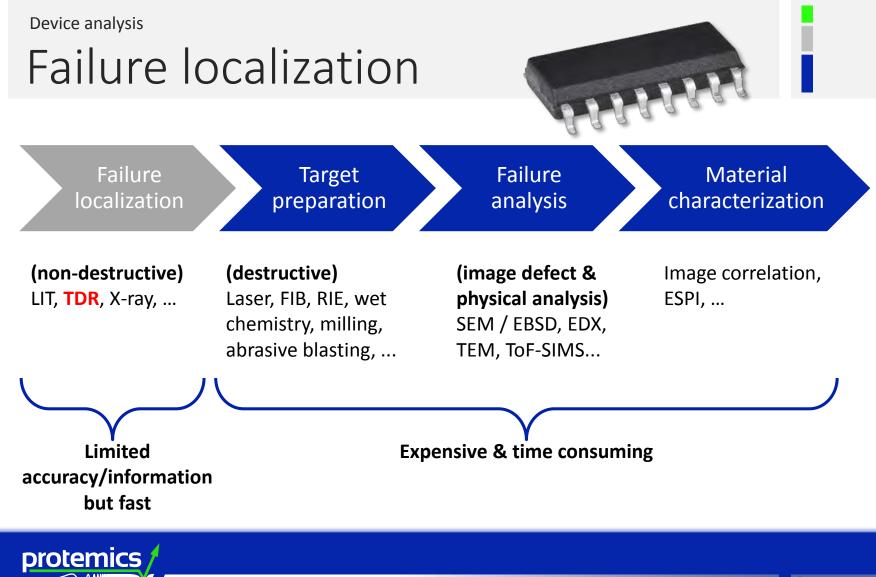
THz on-chip analysis

f=0.202 THz, Phase = 11 °



Frequency-domain measurement data extraction

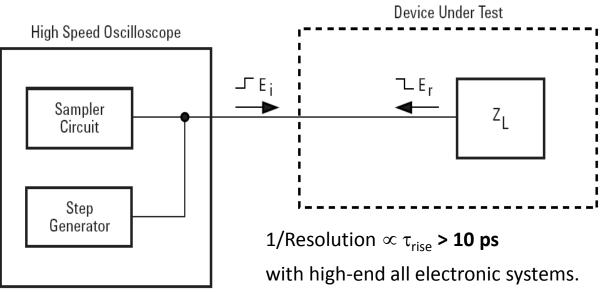




Failure localization



Hewlett-Packard Journal, "Time domain reflectometry" June 1969, Vol. 20, No. 10 TDR principle scheme:



Our Terahertz microprobes achieve up to sub-1 ps rise-times!



Silicon chip

Reflection

THz pulse propagation

Cu-based CPW

PC switch 2

Reflection

THz TDR microprobe

PC switch 1

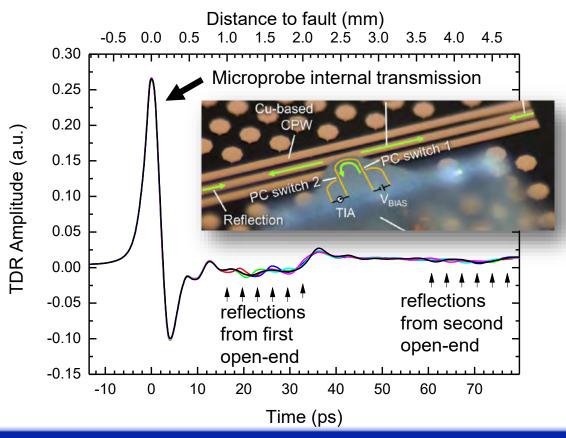
VBIAS

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TIA

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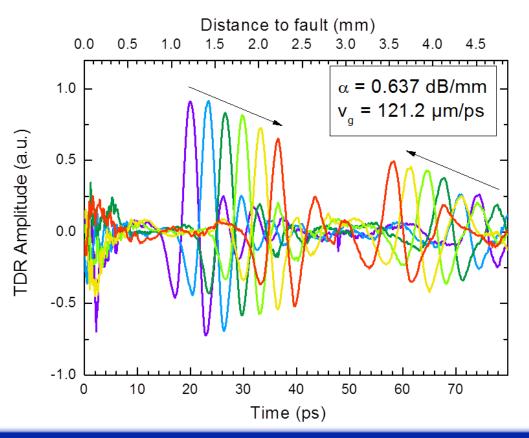
Failure localization



- Internal transmission as reference signal
- Multiple transient scans at different distances to fault
- Reflection signals from short and far distance opens

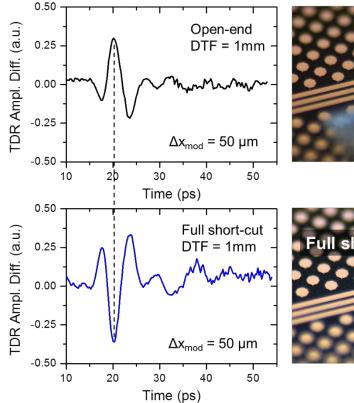
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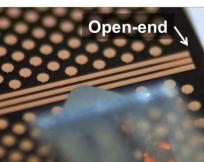
Failure localization



- Suppression of internal transmission signal through distance-to-fault modulation
- Determination of propagation dynamics:
 - Attenuation
 - Group/phase velocities

Failure localization



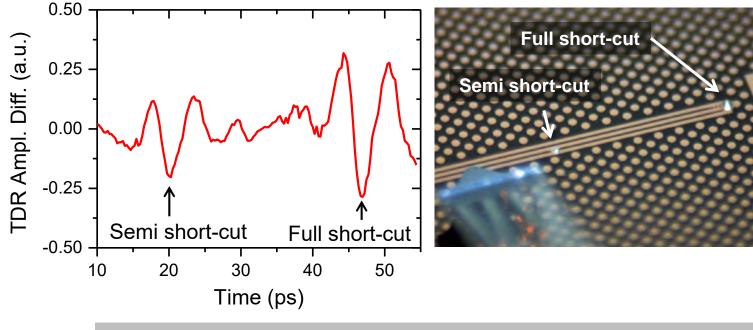


Full short-cut

- Type of fault discremination
- Open vs. Short-cut
- Resistive faults
- Resonant faults



Failure localization



Detection of consecutive faults



Conclusion

- THz microprobes
 - Efficient and versatile tools to avoid inefficient coupling of free-space THz radiation to micro/nanostructures
- Examples: Surface analysis
 - Sheet resistance imaging
 - Non-destructive (contactless), Fast (< 5ms/Pixel)
 - Quantitative (R_{sh} range: 0.1 10000 Ohm)
 - High resolution (ca. 10 μm)
 - Metamaterial-based sensing
 - Increased sensitivity through near-field single element read-out
- Examples: THz device analysis
 - THz on-chip testing: Access to field vector components, amplitude, phase, time- & frequency domain information
 - Failure localization in chip packages: > 10-times increased fault location resolution through sub-ps rise-time THz signals

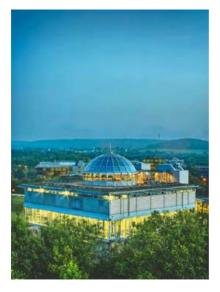


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